

**AMENDMENTS TO THE SPECIFICATION:**

*Please amend paragraph [0004] on page 6, as follows:*

**[0004]** A {0001} surface, which represents a set plane of SiC crystal, includes a (0001) silicon surface 1 and a (000-1) carbon surface 2, which are individual surfaces, as shown in a perspective view of SiC crystal of Fig. 7. In this case, a parenthesized symbol '-' represents a negative sign, which is referred to as polarity. The (0001) silicon surface 1 is a surface in which the crystal is terminated by silicon (Si). The (000-1) carbon surface 2 is a surface in which the crystal is terminated by carbon (C). Nitrogen (N), which is an N-type dopant, is incorporated into the SiC crystal to substitute carbon (C) in most cases. The (0001) silicon surface 1 terminated by silicon is smaller in the quantity of surface-appearing carbon than the (000-1) carbon surface 2 terminated by carbon. Therefore, substitution of carbon into nitrogen (N) is suppressed so that a high-purity epitaxial layer can be obtained. On account of this, most of study reports relating to epitaxial growth of SiC are associated with the ~~(000-1)~~(0001) silicon surface 1.